L Number	Hits	Search Text	DB	Time stamp
-	909	((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and (methor process)	US-PGPUB; EPO; JPO; DERWENT	10:15
_	468	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting	USPAT; US-PGPUB; EPO; JPO;	2002/09/20 09:57
_	403	<pre>injected) ((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting</pre>	DERWENT USPAT; US-PGPUB; EPO; JPO;	2002/09/20 09:58
_	1	<pre>injected)) and (resin encapsulant sealing) (((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting</pre>	DERWENT USPAT; US-PGPUB; EPO; JPO;	2002/09/20 10:08
_	101	<pre>injected)) and (resin encapsulant sealing)) and ((releasable released releasing) nearl (layer film material)) (((((mold near2 (upper lower)) and</pre>	DERWENT USPAT;	2002/09/20
		semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)	US-PGPUB; EPO; JPO; DERWENT	10:03
-	63	<pre>((((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)) and ((flipchip (flip adj chip)) bump ball)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 11:06
-	179		USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:10
_	12	<pre>((mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))) and semiconductor and (chip die wafer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20
-	0	6123895.URPN.	USPAT	2002/09/20 10:16
-	5	("3178807" "5006417" "5384087" "5616421" "5902943").PN.	USPAT	2002/09/20
_		jp408142106a	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:29
_	156	MIYAJIMA-FUMIO	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:30
-	19		USPAT; EPO	2002/09/20 10:30
-	1	6187243.pn. and (parting adj face)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 14:01
_	1481	<pre>(mold near2 (upper lower)) and semiconductor and (chip die wafer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:42
-	39173	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:34
				

-	54	(mold near2 (upper lower)) near3 (air adj vent)	USPAT; US-PGPUB; EPO; JPO;	2002/09/24 14:59
_	8	((mold near2 (upper lower)) near3 (air adj vent)) and semiconductor and (chip	DERWENT USPAT; US-PGPUB;	2002/09/24 14:59
_	5628	die wafer) tab near3 lead	EPO; JPO; DERWENT USPAT;	2002/09/24
			US-PGPUB; EPO; JPO; DERWENT	15:18
-	1951	(tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:33
-	92	((tab near3 lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated plating electroplated electroplating)) with (electrode terminal pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:34
-	21		USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:29
-	3900	257/787	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
_	1339	257/787 and shape	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
_	57	(257/787 and shape) and leadless	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
_	40537	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:40
_	7365	(mold near2 (upper lower)) and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:37
-	4354	((mold near2 (upper lower)) and (chip die wafer)) and (methor process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:39
_	5701	((mold near2 (upper lower)) and (chip die wafer)) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:39
	173	<pre>(((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:45
- ,	0	<pre>((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and ((releasable released releasing) near (film layer tape))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 11:07
-	12		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:36
_	0	20020017738.URPN.	USPAT	2003/03/27 12:20

_	55	die wafer)) and (method process)) and	USPAT; US-PGPUB;	2003/03/27 14:35
-	43	<pre>(flipchip (flip adj chip))) and (releasable released release releasing) (((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and (releasable released release releasing)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and ((releasable released release releasing)</pre>	EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 12:24
_	98	near (film layer tape))) 5450283.URPN.	USPAT	2003/03/27 14:35
-	759	<pre>(((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)</pre>	USPAT	2003/03/27 14:35
	671	<pre>((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))</pre>	USPAT	2003/03/27 14:35
_	275	<pre>(((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not (((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and (releasable released release releasing)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:36
_	10		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:43
-	2	6019588.URPN.	USPAT	2003/03/27 14:41
-	16	("4044984" "4236689" "4332537" "4442056" "4470786" "4697784" "4779835" "5059105" "5118271" "5218759" "5429488" "5484274" "5626886" "5639695" "5693572" "5779958").PN.	USPAT	2003/03/27 14:41
_	265	<pre>((((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and (releasable released release releasing)) not (((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not (((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and ((releasable released release releasing) nearl (film layer tape)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:43
_	1	"20030052418"	USPAT; US-PGPUB; EPO; JPO;	2003/05/08 09:32
-	40999	mold near2 (upper lower)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:41

-	1694	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO;	10:15
-	446	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/05/08 09:45
-	395	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and	DERWENT USPAT; US-PGPUB;	2003/05/08 12:18
	369	(leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)	EPO; JPO; DERWENT	
	369	<pre>((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (method</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26
-	122	process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:47
_	53	process)) and ((die mounting) adj pad) 5474958.URPN.	USPAT	2003/05/08 09:52
_	0	6472252.URPN.	USPAT	2003/05/08
-	36	("4313718" "4697784" "4881884" "4944908" "5147821" "5355283" "5362679" "5405255" "5406699" "5467253" "5468999" "5474958" "5477611" "5479051" "5490324" "5506756" "5508565" "5527743" "5543658" "5545922" "5556807" "5596227" "5609889" "5626886" "5656549" "5663106" "5665281" "5688716" "5766649" "5766650" "5817545" "5876765" "5923959" "5928595" "6117382" "6281588").PN.	USPAT	2003/05/08 09:59
-	3	6117382.URPN.	USPAT	2003/05/08 10:01
-	20	("5034350" "5114880" "5147815" "5222014" "5239806" "5313365" "5331205" "5366364" "5458694" "5488257" "5578261" "5597643" "5598034" "5608262" "5609889" "5614441" "5615089" "5646829" "5755914" "5830781").PN.	USPAT	2003/05/08 10:02
-	20	("5034350" "5114880" "5147815" "5222014" "5239806" "5313365" "5331205" "5366364" "5458694" "5488257" "5578261" "5597643" "5598034" "5608262" "5609889" "5614441" "5615089" "5646829" "5755914" "5830781").PN.	USPAT	2003/05/08 10:04
-	7	5923959.URPN.	USPAT	2003/05/08 10:05
-	20	("5355283" "5362679" "5406699" "5467253" "5468999" "5474958" "5477611" "5479051" "5490324" "5506756" "5508565" "5527743" "5543658" "5545922" "5556807" "5596227" "5609889" "5656549" "5663106" "5688716").PN.	USPAT	2003/05/08
-	21	5609889.URPN.	USPAT	2003/05/08 10:12
-	0	6428300.URPN.	USPAT	2003/05/08 10:13

-	29		USPAT	2003/05/08
		"4184835" "4464322" "4470786"		10:13
		"4618466" "4770833" "4954308"	1	
		"5049344" "5049526" "5110515"		
		"5174941" "5326243" "5344600"		
		"5366368" "5429488" "5451153"		
		"5480296" "5523038" "5558883"		
		"5609889" "5626886" "5650177"		
1		"5714106" "5798070" "5989471"		
	0.5	"6030569" "6224360").PN.		0000 (05 (00
-	26	5817545.URPN.	USPAT	2003/05/08
	_	CEE0000 27777		10:18
-	0	6558982.URPN.	USPAT	2003/05/08
	6	/#5017545# #5074224# #5000242#	IICD N M	10:19
-	٥ ا	("5817545" "5874324" "5998243" "6204095" "6329224" "6335221").PN.	USPAT	2003/05/08
<u> </u>	36	("3930114" "4043027" "4437141"	HCDAE	10:19
1 -	36	(3930114	USPAT	2003/05/08
		"4688152" "4778641" "4823234"		10:23
		"4859722" "4861251" "4868349"		·
		"4890152" "4893172" "4935581"		
		"4954877" "4954878" "4961105"		
		"4972253" "4975765" "5019673"		
		"5049526" "5093282" "5108955"		
1		"5132778" "5136366" "5153385"		
		"5191511" "5216278" "5218759"		
		"5241133" "5296738" "5328870"		
		"5355283" "5370517" "5395226").PN.		
-	40	5108955.URPN.	USPAT	2003/05/08
				10:26
-	7	,	USPAT	2003/05/08
1		"4822550" "4823234" "4868638"		10:43
}		"4890152").PN.		
-	3	6081978.URPN.	USPAT	2003/05/08
	_			12:10
-	3	("5336272" "6001671" "6033933").PN.	USPAT	2003/05/08
	112			12:11
-	113	((((mold near2 (upper lower)) and	USPAT;	2003/05/08
		semiconductor and (chip die wafer)) and	US-PGPUB;	12:18
		(leadframe (lead near1 (inner outer))))	EPO; JPO; DERWENT	
		and (sealing sealed encapsulant encapsulating encapsulated)) and (vent	DEKWENI	
		vacuum)		
_	389176	"113" not (((((mold near2 (upper lower))	USPAT;	2003/05/08
	305170	and semiconductor and (chip die wafer))	US-PGPUB;	12:19
		and (leadframe (lead nearl (inner	EPO; JPO;	12.13
		outer)))) and (sealing sealed encapsulant	DERWENT	
		encapsulating encapsulated)) and (method		
		process)) and ((die mounting) adj pad))		
-	91	(((((mold near2 (upper lower)) and	USPAT;	2003/05/08
		semiconductor and (chip die wafer)) and	US-PGPUB;	12:19
		(leadframe (lead nearl (inner outer))))	EPO; JPO;	
		and (sealing sealed encapsulant	DERWENT	
		encapsulating encapsulated)) and (vent		
		vacuum)) not ((((((mold near2 (upper		
		lower)) and semiconductor and (chip die		
		wafer)) and (leadframe (lead near1 (inner		
		outer)))) and (sealing sealed encapsulant		
		encapsulating encapsulated)) and (method		
		process)) and ((die mounting) adj pad))		2222/25/22
_	25	5147821.URPN.	USPAT	2003/05/08
		/!! 4966E06!! !! 4044009!! \ DX	IICDAM	12:24
_	2	("4866506" "4944908").PN.	USPAT	2003/05/08 12:26
_	25	5147821.URPN.	USPAT	2003/05/08
_	23	JIT/UZI.UKFN.	USPAI	13:43
_	53	5474958.URPN.	USPAT	2003/05/08
		31,190.0MIN.	SPIRI	13:44
_	4	5776800.URPN.	USPAT	2003/05/08
	•			13:45

-	5	("5101324" "5130889" "5309026"	USPAT	2003/05/08
		"5394298" "5474958").PN.		13:45
-	2	5874319.URPN.	USPAT	2003/05/08
				13:48
-	21	("3777365" "3811182" "4881885"	USPAT	2003/05/08
		"4932883" "5147821" "5173451"		13:48
		"5203401" "5237269" "5322207"		
		"5336649" "5367253" "5378981"		
		"5424652" "5459351" "5474958"	1	
		"5475317" "5489538" "5548884"		
		"5568057" "5589781" "5591649").PN.		
	2	("4866506" "4944908").PN.	*****	2002/05/00
-		("4866506" "4944906").PN.	USPAT	2003/05/08
i		/#4066506# #4044000#\ my		13:53
-	2	("4866506" "4944908").PN.	USPAT	2003/05/08
	_	" () () () ()	l	13:53
-	5	"6081978"	USPAT;	2003/05/12
			US-PGPUB;	09:17
			EPO; JPO;	
			DERWENT	
-	3	("5336272" "6001671" "6033933").PN.	USPAT	2003/05/12
1				08:46
-	740	(memory adj chip) near3 array	USPAT;	2003/05/12
		_	US-PGPUB;	09:36
			EPO; JPO;	
1			DERWENT	
-	471	((memory adj chip) near3 array) and	USPAT;	2003/05/12
]		semiconductor	US-PGPUB;	09:18
	}		EPO; JPO;	"
			DERWENT	
 	137	((memory adj chip) near3 array) and	USPAT;	2003/05/12
	13,	(semiconductor near1 (package device))	US-PGPUB;	09:20
		(Semiconductor hearr (package device))		09:20
			EPO; JPO;	
		//manage and abin) manage and a sign	DERWENT	2002 (05 (12
-	8	((memory adj chip) near3 array) with	USPAT;	2003/05/12
		known	US-PGPUB;	09:37
			EPO; JPO;	ļ .
			DERWENT	
-	1406	(memory near chip) near4 array	USPAT;	2003/05/12
			US-PGPUB;	09:36
			EPO; JPO;	
			DERWENT	[
-	15	((memory near chip) near4 array) with	USPAT;	2003/05/12
		known	US-PGPUB;	09:37
			EPO; JPO;	l i
			DERWENT	
-	7	(((memory near chip) near4 array) with	USPAT;	2003/05/12
		known) not (((memory adj chip) near3	US-PGPUB;	09:37
		array) with known)	EPO; JPO;	
		, ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	DERWENT	
-	2102	(tab near3 lead) and semiconductor and	USPAT;	2003/05/19
		(chip die wafer)	US-PGPUB;	08:33
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT	
_	1640	((tab near3 lead) and semiconductor and	USPAT;	2003/05/19
	10.0	(chip die wafer)) and (lead with	US-PGPUB;	08:36
		(electrode bump ball terminal pad))	EPO; JPO;	**.30
		(orocoroac pamp part cerminal pad)	DERWENT	
_	123	(((tab near3 lead) and semiconductor and	USPAT;	2004/01/26
	123	(chip die wafer)) and (lead with		10:18
			US-PGPUB;	10.10
	ļ	(electrode bump ball terminal pad))) and	EPO; JPO;	
		(conductive nearl (vias (through adj	DERWENT	
		hole)))	*****	0004/01/05
-	94	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2004/01/26
		(chip die wafer)) and (lead with	US-PGPUB;	10:18
		(electrode bump ball terminal pad))) and	EPO; JPO;	
		(conductive nearl (vias (through adj	DERWENT	
	ļ	hole)))) and (seal sealed sealing		
		encapsulant encapsulated encapsulating)		

	·····	Y		
-	43	(((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with	USPAT; US-PGPUB;	2003/05/19 08:38
1		(electrode bump ball terminal pad))) and	EPO; JPO;	08:38
		(conductive near1 (vias (through adj	DERWENT	
		hole)))) and (seal sealed sealing	DEKWERT	
		encapsulant encapsulated encapsulating))		1
1		and (stacked stacking)		
-	1916	(mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)	US-PGPUB;	10:15
	•		EPO; JPO;	
			DERWENT	· .
-	1562	((mold near2 (upper lower)) and	USPAT;	2004/01/26
i		semiconductor and (chip die wafer)) and	US-PGPUB;	10:16
		(method process)	EPO; JPO;	
	430	///mald magn2 (symman lasses)) and	DERWENT	2004/01/26
-	430	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and	USPAT;	2004/01/26
		(method process)) and (leadframe (lead	US-PGPUB; EPO; JPO;	10:17
		nearl (inner outer))) and (sealing sealed	DERWENT	
		encapsulant encapsulating encapsulated)	~~~~	
-	232		USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
! !		(method process)) and (leadframe (lead	EPO; JPO;	
		near1 (inner outer))) and (sealing sealed	DERWENT	
ł		encapsulant encapsulating encapsulated))		
		and (vias (through adj hole))		
-	49	(((((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO; DERWENT	
		nearl (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated))	DEKWENI	`
		and (vias (through adj hole))) and		
		((reducing near1 thickness) thinning)		
[-	129	((((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO;	
		nearl (inner outer))) and (sealing sealed	DERWENT	
[encapsulant encapsulating encapsulated))		
_	77	and (stacked stacking)	HCDAM -	2004/01/26
-	′′	(((((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead	US-PGPUB; EPO; JPO;	10.22
		nearl (inner outer))) and (sealing sealed	DERWENT	
		encapsulant encapsulating encapsulated))		
		and (stacked stacking)) and (vias		
		(through adj hole))		
-	45	(((((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO;	
		near1 (inner outer))) and (sealing sealed	DERWENT	
		<pre>encapsulant encapsulating encapsulated)) and (stacked stacking)) and (vias</pre>		
		(through adj hole))) not (((((mold near2		
		(upper lower)) and semiconductor and		
		(chip die wafer)) and (method process))		
		and (leadframe (lead near1 (inner		
		outer))) and (sealing sealed encapsulant		
		encapsulating encapsulated)) and (vias		
		(through adj hole))) and ((reducing near1		
L,		thickness) thinning))		